

3CG640, 3CG708**PNP Silicon High Frequency Middle Power Transistor****Features:**

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit. Make up push pull amplifying circuit with NPN.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications	
			3CG640	3CG708
Total Dissipation	P_{tot}	mW	1000 (Ta=25°C)	800 (Ta=25°C)
Max. Collector Current	I_{CM}	mA	1500	600
Junction Temperature	T_{jm}	°C	175	175
Storage Temperature	T_{stg}	°C	-55~+175	-55~+175
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	80 (Ic=0.1mA)	60(Ic=0.1mA)
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	≥5 (IE=0.1mA)	≥8 (IE=0.1mA)
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.5	0.7
			Ic=500mA, Ib=50mA	Ic=500mA, Ib=50mA
C-E Leakage Current	I_{CEO}	uA	1.0	1.0
			$V_{CE}=30V$	$V_{CE}=30V$
DC Current Gain	h_{FE}		25~270	25~270
			$V_{CE}=5V, I_c=200mA$	$V_{CE}=2V, I_c=50mA$
Transition frequency	f_T	MHz	100	100
			$V_{CE}=10V, I_c=50mA, f=30MHz$	$V_{CE}=10V, I_c=50mA, f=30MHz$

hFE Colored:

Color	Orange	Yellow	Green	Blue	Purple	Gray
h_{FE}	25~40	40~55	55~80	80~120	120~180	180~270

Outline and Dimensions: